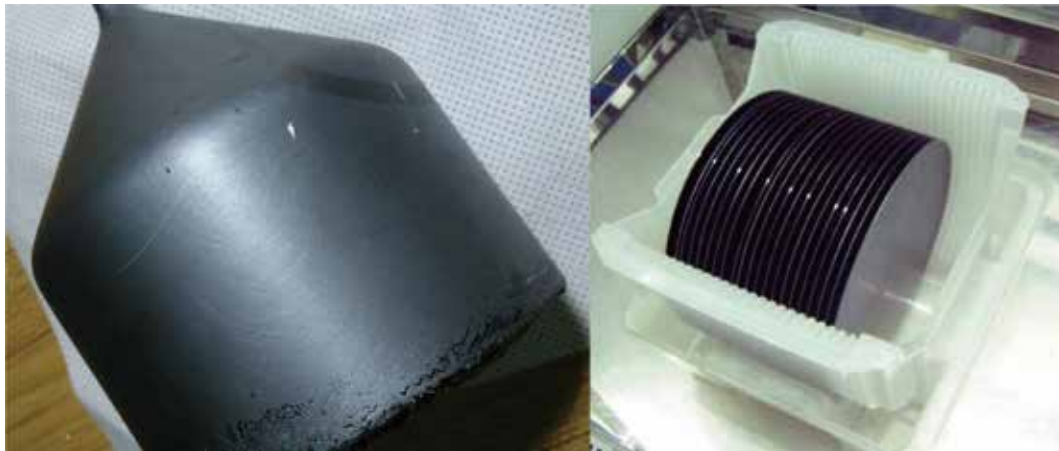


InP-Indium Phosphide



Electrical and Dopant Specifications				
Dopant	Type	Carrier concentration (cm ⁻³)	Mobility (cm ² V ⁻¹ s ⁻¹)	E.P.D (cm ⁻²)
Undoped	n-type	$\leq 3 \times 10^{16}$	$(3.5-4) \times 10^3$	≤ 500
S-InP	n-type	$(0.8-6) \times 10^{18}$	$(1.5-3.5) \times 10^3$	≤ 500
Zn-InP	P-type	$(0.6-6) \times 10^{18}$	50-70	≤ 500
Fe-InP	SI	Resistivity $> 1 \times 10^7 \Omega \cdot \text{cm}$	> 2000	≤ 500

InP Wafer Specifications			
Size	2"	3"	4"
Diameter(mm)	50.5±0.5	76.2±0.5	100.0±0.5
Thickness(um)	350±25	600±25	600±25
Orientation	(100)/(111) ±0.5°		
Major Flat Length(mm)	16±2	22±2	32.5±2
Minor Flat length(mm)	8±1	11±1	18±1
TTV(um)	<10	<10	<15
Bow(um)	<10	<10	<15
Warp(um)	<15	<15	<15